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(ISPSD 2012)

**Bruges, Belgium
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Don Disney (Avogy, USA)

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Samir Mouhoubi¹, Y. Wu², F. Bauwens¹, J. Roig¹, P. Gassot¹, M. Tack¹

¹*Power Technology Centre, ON Semiconductor, Belgium*

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¹*TSMC, Taiwan*

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²*Texas Instruments, United States of America*

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¹Mitsubishi Electric Corporation, Japan

²Mitsubishi Electric Information Network Corporation, Japan

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¹Fuji Electric Co. Ltd., Japan

²Nakagawa Consulting Office, LLC., Japan

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¹MESA+ Institute for Nanotechnology University of Twente The Netherlands, The Netherlands

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¹University of Electronic Science and Technology of China, China

²Tianjin Zhonghuan Semiconductor Co. Ltd., China

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¹ICSEAD, Japan

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¹Austriamicrosystems AG, Austria

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¹University of Electronic Science and Technology of China, China

²No.58 Research Institute, China Electronics Technology Group Corporation, China

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¹Renesas Electronics, Japan

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09:00 - 10:40

Low Voltage 2 - Reliability Physics

Chairs: Gary Dolny (Fairchild Semiconductor, USA)

Johnny Sin (Hong Kong University of Science and Technology, Hong Kong)

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¹University of Texas Arlington, United States of America
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¹IBM India Pvt Ltd, India
²IBM, United States of America 315

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Phil Mawby (University of Warwick, UK)

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Wide Bandgap Devices 2 - GaN Devices 2

Chairs: Nariaki Ikeda (Furukawa Electric, Japan)

Paul Chow (Rensselaer Polytechnic Institute, USA)

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- 13:30 - 13:55 **WBG2-1 • Mechanisms responsible for dynamic ON-resistance in GaN high-voltage HEMTs**
Donghyun Jin, Jesus del Alamo
Massachusetts Institute of Technology, United States of America 333

13:55 - 14:20	<p>WBG2-2 • Breakdown Voltage Enhancement for Power AlGaIn/GaN HEMTs with Air-bridge Field Plate <u>Gang Xie</u>¹, Edward Xu¹, Junmin Lee¹, Niloufar Hashemi¹, Fred Y. Fu², Bo Zhang³, Wai Tung Ng¹ ¹University of Toronto, Canada ²Crosslight software Inc, Canada ³University of Electronic Science and Technology of China, China</p>	337
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14:45 - 15:10	<p>WBG2-4 • Impact of Buffer Composition on the Dynamic On-State Resistance of High-Voltage AlGaIn/GaN HFETs <u>Oliver Hilt</u>, Eldad Bahat-Treidel, Eunjung Cho, Sebastian Singwald, Joachim Würfl FBH Berlin, Germany</p>	345
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